Supporting Information

Negative Differential Resistance Observed on the Charge Density Wave of a Transition Metal Dichalcogenide

Adina Luican-Mayer^{1+3*}, Yuan Zhang¹⁺, Andrew DiLullo¹, Yang Li^{1,2}, Brandon Fisher¹, Sergio E. Ulloa², and Saw-Wai Hla^{1,2,*}

¹Center for Nanoscale Materials, Argonne National Laboratory, 9700 South Cass Ave., Argonne, Illinois 60439, United States.

²Nanoscale and Quantum Phenomena Institute, and Department of Physics & Astronomy, Ohio University, Athens, Ohio 45701, United States.

³Department of Physics, University of Ottawa, 150 Louis Pasteur Private, Ottawa, Canada.

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Corresponding Author

* Corresponding authors email: hla@ohio.edu ; luican-mayer@uottaw.ca

Present Addresses

⁺Current Address: Department of Physics, Old Dominion University, 4600 Elkhorn Ave, Norfolk, VA

23529, USA.

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S1. Stacking or CDW in adjacent 1T-TaS₂ layers



Figure S1. STM image of 1T-TaS₂ multi-layers acquired at the edge of the sample shows CDW domains. The triangles indicate different ordering [Imaging parameters: $V_t = 1V$, $I_t = 1$ nA].

S2. Creation of tip-induced local defects



Figure S2. *a*, An STM image of a 1T-TaS₂ with the CDW lattice. *b*, The STM image after creating two point defects at the place shown with red arrows in 'a'. The brighter regions (indicated with a white arrow) are stacking faults caused by the manipulation. *c*, A zoom in STM image after creating another defect at the blue arrow location in 'b'. White ovals indicate the changes in electronic structure of the CDW top sites that exhibit NDR. The green oval in 'a' and 'c' indicate the same CDW top site before and after manipulation where the dI/dV spectra shown in Fig. 3b are acquired. [Imaging parameters: $V_t = 1V$, $I_t = 0.2$ nA].

S3. 1T-TaS₂ region of the dI/dV movie



Figure S3. *a*, An STM image of 1T-TaS₂ region after tip sample mechanical contact at left (indicated with the white arrow). *b*, dl/dV maps are acquired at the green rectangle region. *c*, An STM image of the same 1T-TaS₂ region where a CDW domain is indicated with the white dashed line. *d*, A line profile across the blue line in '*c*' shows a height difference appeared at the domain wall (indicated with red arrows in 'c' and 'd'). The red oval in '*a*', '*b*' and '*c*' marks the position of a bright protrusion (electronic defect) used here as a landmark. [Imaging parameters: $V_t = 1V$, $I_t = 1$ nA]

S4. dI/dV spectroscopy of individual atoms



Figure S4. dI/dV spectra acquired over the 'a' (green), 'b' (pink) and 'c' (yellow) atom sites of the Star-of-David structure. The average spectrum of each atom type; green for 'a', brown for 'b' and orange for 'c' atoms.

S5. Tip height dependent dI/dV spectroscopy



Figure S5. dI/dV spectroscopic data measured at different set-currents at a fixed bias of 1V. The increase in tunnelling current represents an approaching tip towards the surface. **a**, dI/dV curves measured at the different set tunnelling currents on the CDW top site (a defect site as shown in Fig. 2a) reveal an increasing NDR at ~0.5 V (indicated with a red arrow) by reducing the tip height. **b**, dI/dV curves measured at a CDW top site that does not show NDR. Here, the dI/dV curves remain at positive values at ~0.5 V by approaching the tip to the surface (red arrow location).